

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Chung Wai Leung et al.
Assignee: Mosel Vitelic, Inc.
Title: Nonvolatile Memory Structures and Fabrication Methods
Application No.: Unknown Filing Date: Herewith
Examiner: Unknown Group Art Unit: Unknown
Docket No.: M-11467-2D US

San Jose, California
October 20, 2003

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(b)

Dear Sir:

Pursuant to 37 CFR § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying form PTO-1449 are called to the attention of the Examiner for the above patent application. Copies of these documents are not enclosed as all documents were previously cited by or submitted to the Patent Office in prior applications relied upon for priority under 35 U.S.C. 120(37 C.F.R. § 1.98(d)). The prior applications are U.S. Application No. 10/200,443, filed July 22, 2002, and U.S. Application No. 09/969,841 filed October 2, 2001.

Citation of these documents shall not be construed as:

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2. a representation that a search has been made, other than as described above; or
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Respectfully submitted,

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Reg. No. 34,250

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| (Use several sheets if necessary) | | | | Leung et al. | | | |
| | | | | Filing Date | | Group | |
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